Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!


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Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

# NDD04N50Z

# N-Channel Power MOSFET 500 V, 2.7 Ω

**Features**

- Low ON Resistance
- Low Gate Charge
- ESD Diode−Protected Gate
- 100% Avalanche Tested
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Drain−to−Source Voltage | $V_{DSS}$ | 500 | V |
| Continuous Drain Current $R_{\theta JC}$ | $I_D$ | 3.0 | A |
| Continuous Drain Current $R_{\theta JC}$, $T_A$ = 100°C | $I_D$ | 1.9 | A |
| Pulsed Drain Current, $V_{GS}$ @ 10 V | $I_{DM}$ | 12 | A |
| Power Dissipation $R_{\theta JC}$ | $P_D$ | 61 | W |
| Gate−to−Source Voltage | $V_{GS}$ | ±30 | V |
| Single Pulse Avalanche Energy, $I_D$ = 3.4 A | $E_{AS}$ | 120 | mJ |
| ESD (HBM) (JESD22−A114) | $V_{esd}$ | 2800 | V |
| Peak Diode Recovery | dv/dt | 4.5 (Note 1) | V/ns |
| Continuous Source Current (Body Diode) | $I_S$ | 3.4 | A |
| Maximum Temperature for Soldering Leads | $T_L$ | 260 | °C |
| Operating Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | −55 to 150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $I_D \le 3.4$ A, di/dt ≤ 200 A/μs, $V_{DD} \le BV_{DSS}$, $T_J \le 150$°C.

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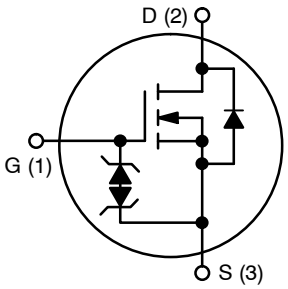
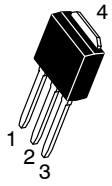
**http://onsemi.com**

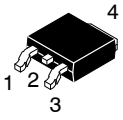
| $V_{DSS}$ | $R_{DS(on)}$ (MAX) @ 1.5 A |
|---|---|
| 500 V | 2.7 Ω |

**N−Channel**




**IPAK**
**CASE 369D**
**STYLE 2**




**DPAK**
**CASE 369AA**
**STYLE 2**

## MARKING AND ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

## THERMAL RESISTANCE

| Parameter | | Symbol | Value | Unit |
|---|---|---|---|---|
| Junction−to−Case (Drain) | NDD04N50Z | $R_{\theta JC}$ | 2.0 | °C/W |
| Junction−to−Ambient Steady State | (Note 3) NDD04N50Z<br>(Note 2) NDD04N50Z−1 | $R_{\theta JA}$ | 40<br>80 | |

2. Insertion mounted
3. Surface mounted on FR4 board using 1″ sq. pad size, (Cu area = 1.127 in sq [2 oz] including traces).

## ELECTRICAL CHARACTERISTICS ($T_J$ = 25°C unless otherwise noted)

| Characteristic | Symbol | Test Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 1 mA | | 500 | | | V |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_J$ | Reference to 25°C, $I_D$ = 1 mA | | | 0.6 | | V/°C |
| Drain−to−Source Leakage Current | $I_{DSS}$ | $V_{DS}$ = 500 V, $V_{GS}$ = 0 V | 25°C | | | 1.0 | μA |
| | | | 150°C | | | 50 | |
| Gate−to−Source Forward Leakage | $I_{GSS}$ | $V_{GS}$ = ±20 V | | | | ±10 | μA |
| **ON CHARACTERISTICS** (Note 4) | | | | | | | |
| Static Drain−to−Source On−Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 1.5 A | | | 2.3 | 2.7 | Ω |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 50 μA | | 3.0 | | 4.5 | V |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 15 V, $I_D$ = 1.5 A | | | 2.1 | | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | | |
| Input Capacitance (Note 5) | $C_{iss}$ | $V_{DS}$ = 25 V, $V_{GS}$ = 0 V, f = 1.0 MHz | | 246 | 308 | 370 | pF |
| Output Capacitance (Note 5) | $C_{oss}$ | | | 33 | 43 | 53 | |
| Reverse Transfer Capacitance (Note 5) | $C_{rss}$ | | | 7.0 | 9.0 | 11 | |
| Total Gate Charge (Note 5) | $Q_g$ | $V_{DD}$ = 250 V, $I_D$ = 3.4 A, $V_{GS}$ = 10 V | | 6.0 | 12 | 18 | nC |
| Gate−to−Source Charge (Note 5) | $Q_{gs}$ | | | 1.3 | 2.6 | 4.0 | |
| Gate−to−Drain (“Miller”) Charge (Note 5) | $Q_{gd}$ | | | 3.5 | 6.1 | 7.0 | |
| Plateau Voltage | $V_{GP}$ | | | | 6.6 | | V |
| Gate Resistance | $R_g$ | | | 1.8 | 5.4 | 16.2 | Ω |
| **RESISTIVE SWITCHING CHARACTERISTICS** | | | | | | | |
| Turn−On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 250 V, $I_D$ = 3.4 A, $V_{GS}$ = 10 V, $R_G$ = 5 Ω | | | 9.0 | | ns |
| Rise Time | $t_r$ | | | | 9.0 | | |
| Turn−Off Delay Time | $t_{d(off)}$ | | | | 16 | | |
| Fall Time | $t_f$ | | | | 10 | | |
| **SOURCE−DRAIN DIODE CHARACTERISTICS** ($T_C$ = 25°C unless otherwise noted) | | | | | | | |
| Diode Forward Voltage | $V_{SD}$ | $I_S$ = 3.4 A, $V_{GS}$ = 0 V | | | | 1.6 | V |
| Reverse Recovery Time | $t_{rr}$ | $V_{GS}$ = 0 V, $V_{DD}$ = 30 V, $I_S$ = 3.4 A, di/dt = 100 A/μs | | | 240 | | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | | | 0.9 | | μC |

4. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.
5. Guaranteed by design.

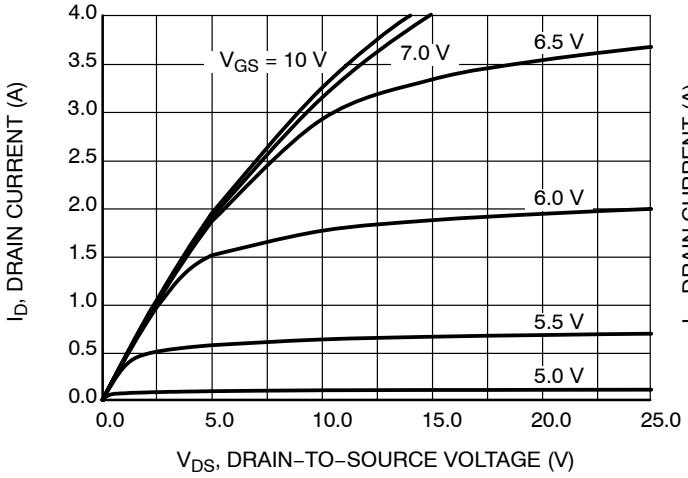



**Figure 1. On−Region Characteristics**

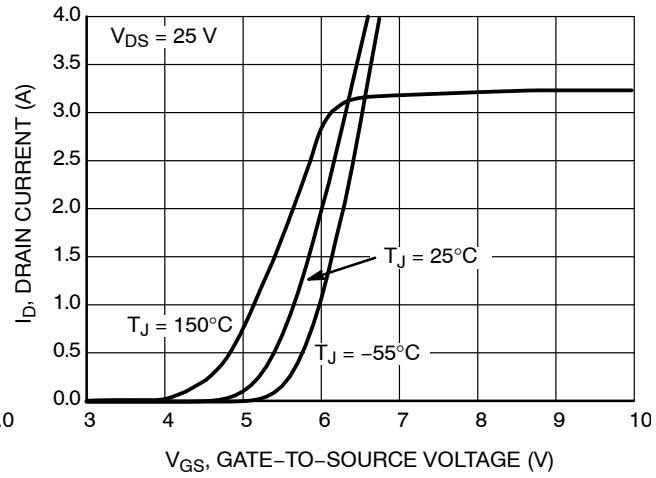



**Figure 2. Transfer Characteristics**

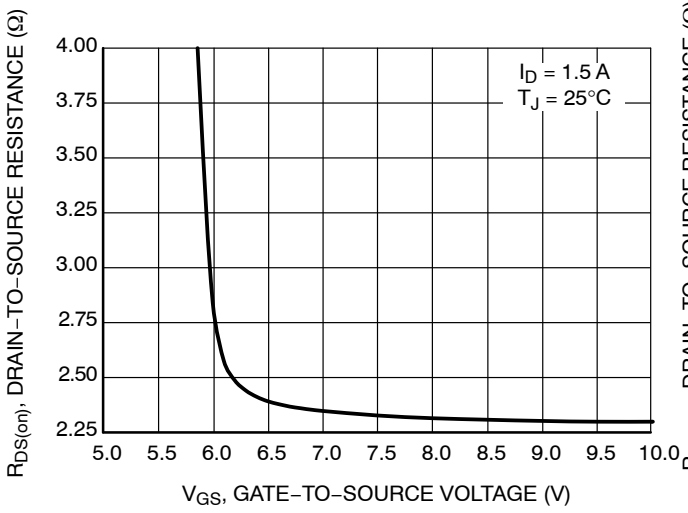



**Figure 3. On−Region versus Gate−to−Source Voltage**

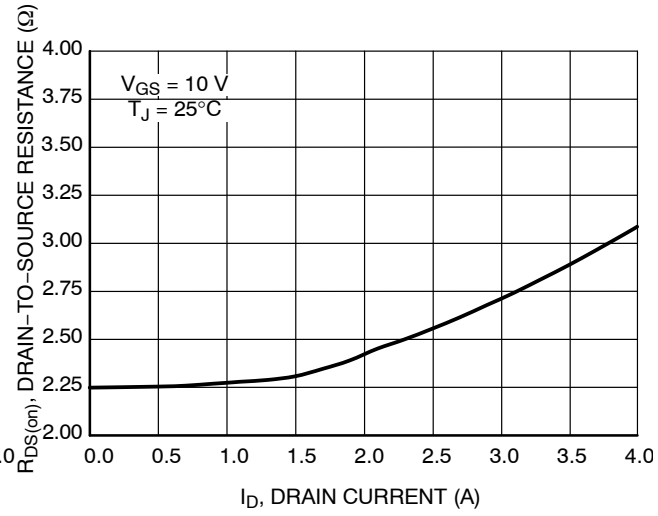



**Figure 4. On−Resistance versus Drain Current and Gate Voltage**

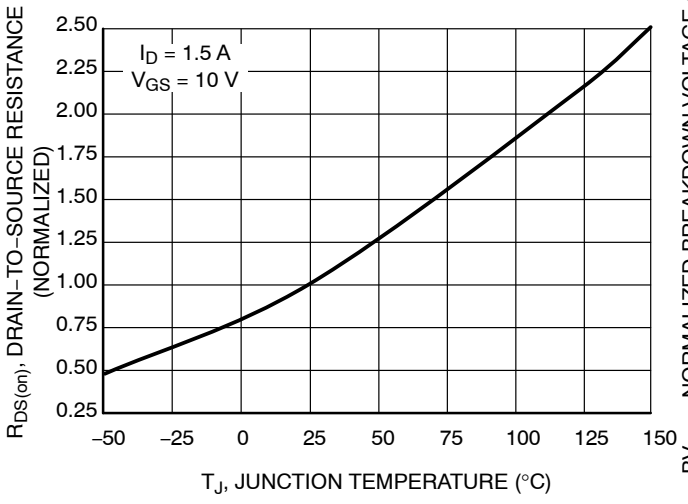



**Figure 5. On−Resistance Variation with Temperature**

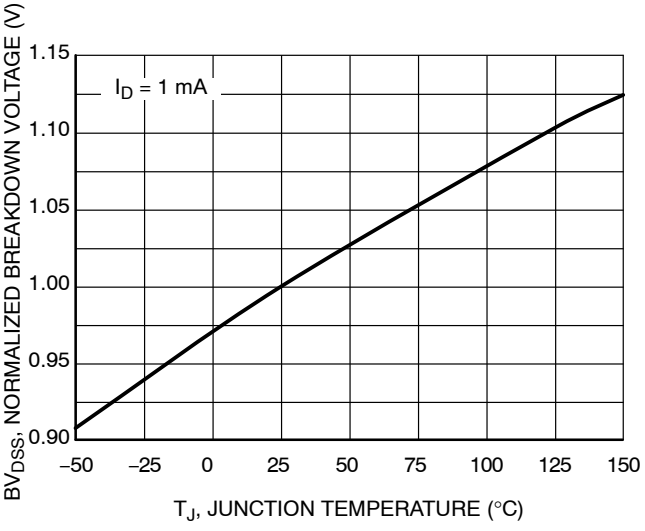



**Figure 6. $BV_{DSS}$ Variation with Temperature**

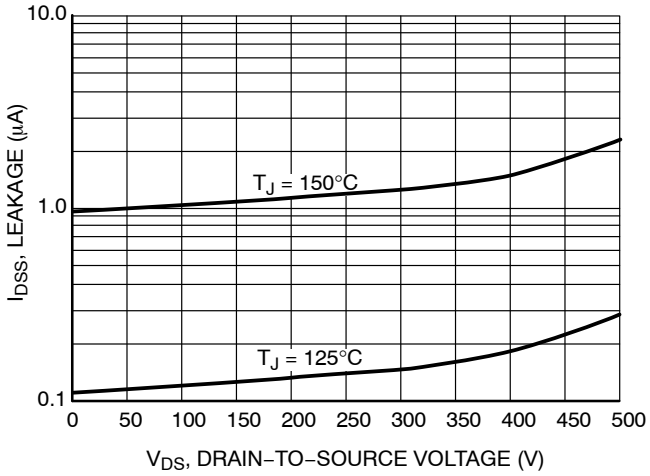



**Figure 7. Drain−to−Source Leakage Current versus Voltage**

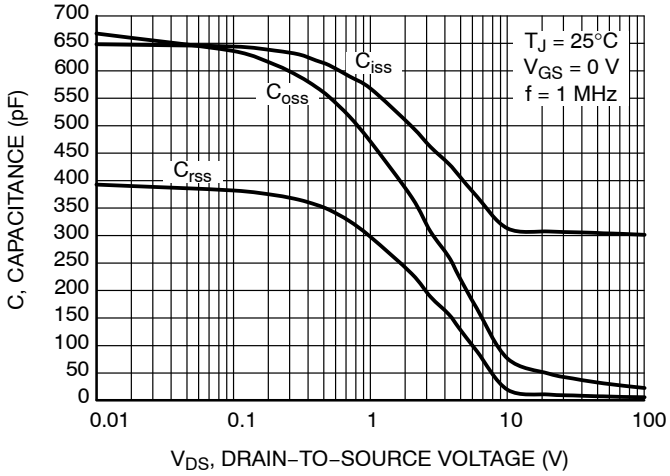



**Figure 8. Capacitance Variation**

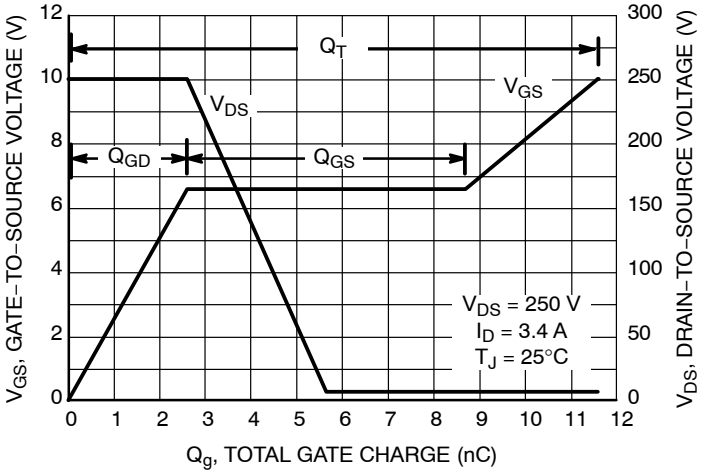



**Figure 9. Gate−to−Source Voltage and Drain−to−Source Voltage versus Total Charge**

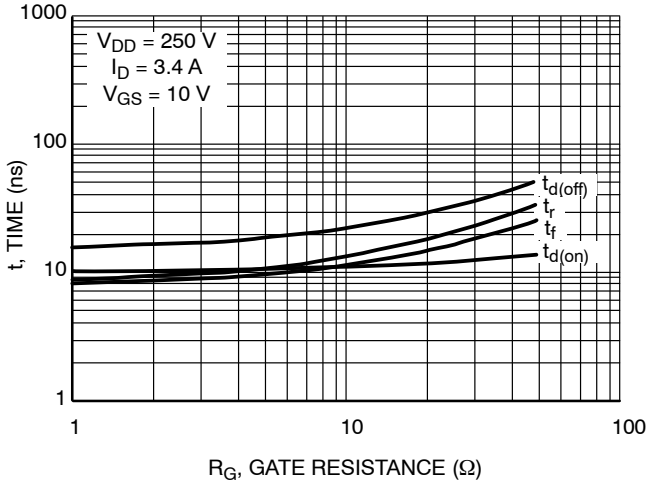



**Figure 10. Resistive Switching Time Variation versus Gate Resistance**

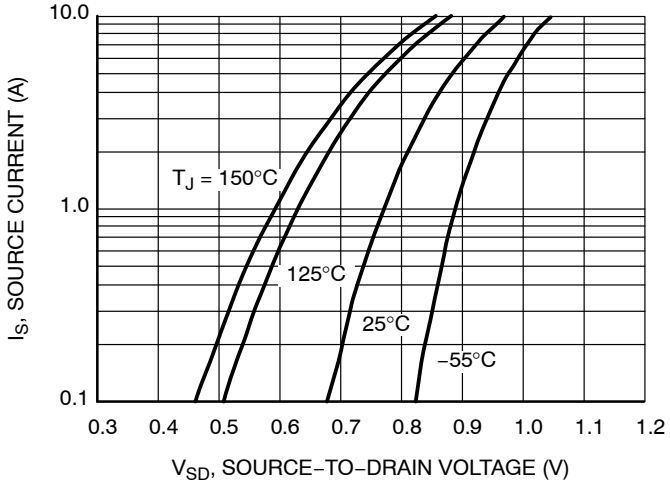



**Figure 11. Diode Forward Voltage versus Current**

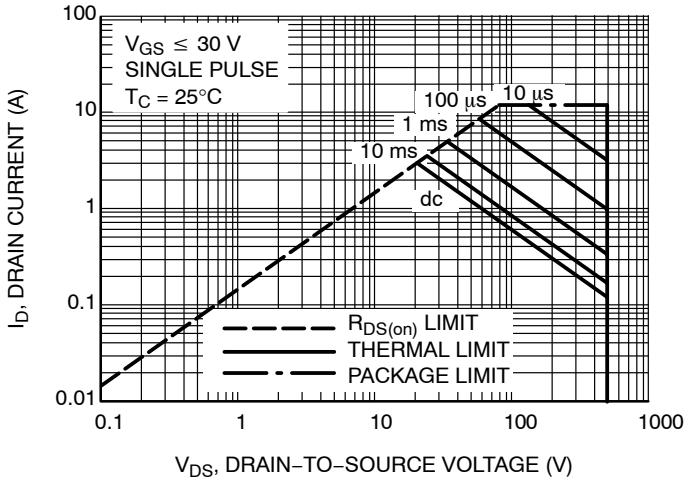



**Figure 12. Maximum Rated Forward Biased Safe Operating Area NDD04N50Z**

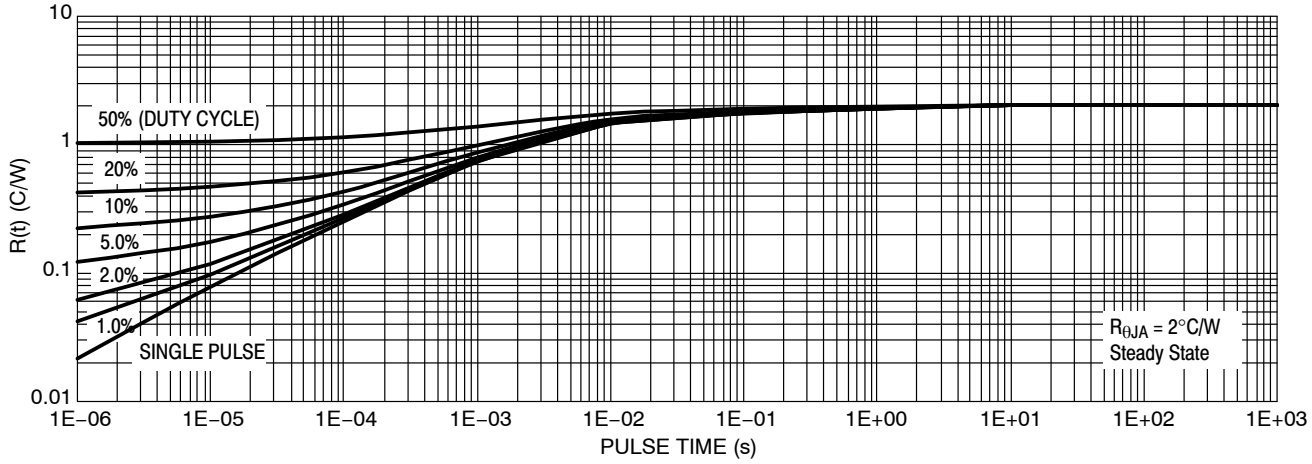



**Figure 13. Thermal Impedance (Junction−to−Case) for NDD04N50Z**

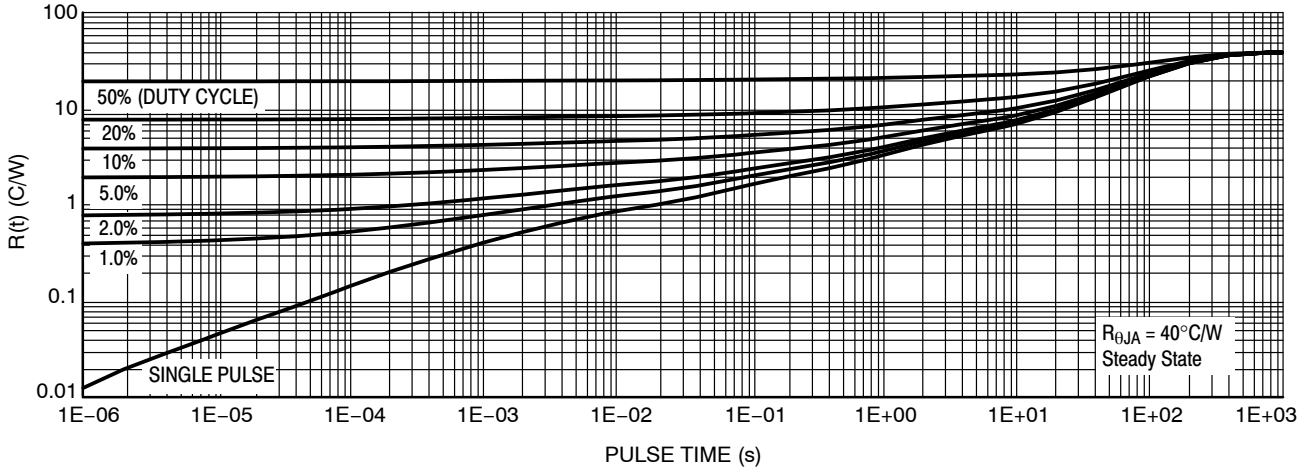


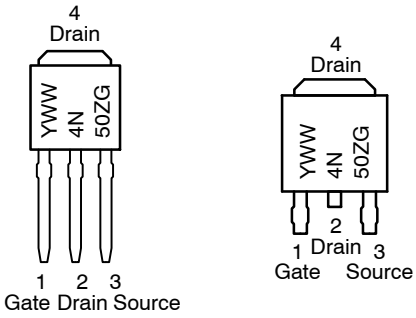

**Figure 14. Thermal Impedance (Junction−to−Ambient) for NDD04N50Z**

## ORDERING INFORMATION

| Order Number | Package | Shipping† |
|---|---|---|
| NDD04N50Z−1G | IPAK<br>(Pb−Free) | 75 Units / Rail |
| NDD04N50ZT4G | DPAK<br>(Pb−Free) | 2500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

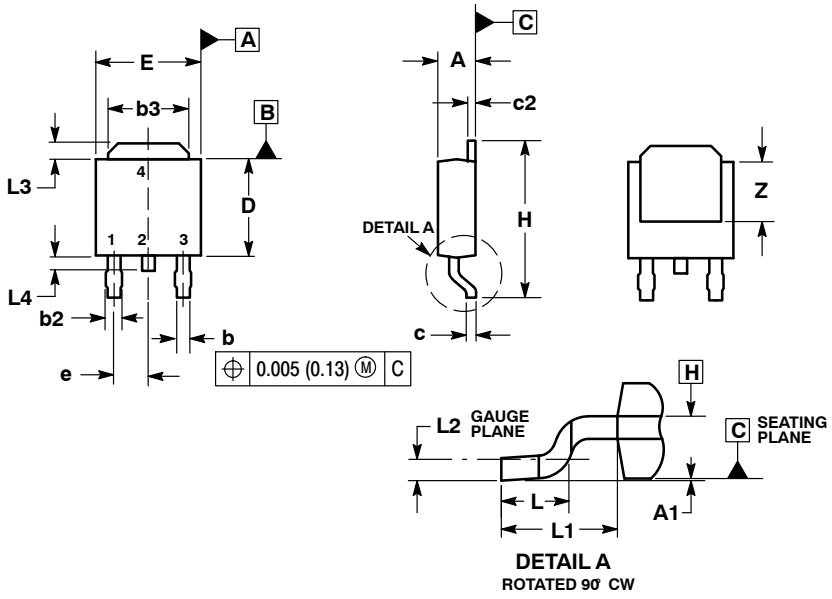
## MARKING DIAGRAMS




| | |
|---|---|
| A | = Location Code |
| Y | = Year |
| WW | = Work Week |
| G | = Pb−Free Package |

## PACKAGE DIMENSIONS

**DPAK (SINGLE GUAGE)**
CASE 369AA−01
ISSUE B

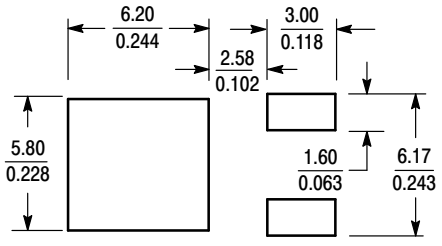



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 0.086 | 0.094 | 2.18 | 2.38 |
| A1 | 0.000 | 0.005 | 0.00 | 0.13 |
| b | 0.025 | 0.035 | 0.63 | 0.89 |
| b2 | 0.030 | 0.045 | 0.76 | 1.14 |
| b3 | 0.180 | 0.215 | 4.57 | 5.46 |
| c | 0.018 | 0.024 | 0.46 | 0.61 |
| c2 | 0.018 | 0.024 | 0.46 | 0.61 |
| D | 0.235 | 0.245 | 5.97 | 6.22 |
| E | 0.250 | 0.265 | 6.35 | 6.73 |
| e | 0.090 BSC | | 2.29 BSC | |
| H | 0.370 | 0.410 | 9.40 | 10.41 |
| L | 0.055 | 0.070 | 1.40 | 1.78 |
| L1 | 0.108 REF | | 2.74 REF | |
| L2 | 0.020 BSC | | 0.51 BSC | |
| L3 | 0.035 | 0.050 | 0.89 | 1.27 |
| L4 | −−− | 0.040 | −−− | 1.01 |
| Z | 0.155 | −−− | 3.93 | −−− |

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

### SOLDERING FOOTPRINT*

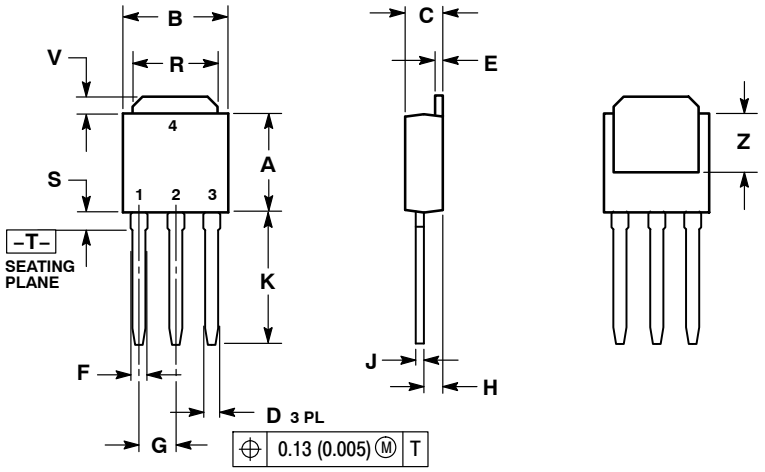



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

**IPAK**
CASE 369D−01
ISSUE B




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 0.235 | 0.245 | 5.97 | 6.35 |
| B | 0.250 | 0.265 | 6.35 | 6.73 |
| C | 0.086 | 0.094 | 2.19 | 2.38 |
| D | 0.027 | 0.035 | 0.69 | 0.88 |
| E | 0.018 | 0.023 | 0.46 | 0.58 |
| F | 0.037 | 0.045 | 0.94 | 1.14 |
| G | 0.090 BSC | | 2.29 BSC | |
| H | 0.034 | 0.040 | 0.87 | 1.01 |
| J | 0.018 | 0.023 | 0.46 | 0.58 |
| K | 0.350 | 0.380 | 8.89 | 9.65 |
| R | 0.180 | 0.215 | 4.45 | 5.45 |
| S | 0.025 | 0.040 | 0.63 | 1.01 |
| V | 0.035 | 0.050 | 0.89 | 1.27 |
| Z | 0.155 | −−− | 3.93 | −−− |

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN



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**Fax**: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
**Email**: orderlit@onsemi.com

**N. American Technical Support**: 800−282−9855 Toll Free USA/Canada
**Europe, Middle East and Africa Technical Support:**
Phone: 421 33 790 2910
**Japan Customer Focus Center**
Phone: 81−3−5773−3850

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